

SINGLE CHIP FOR BLUETOOTH & FM RADIO TUNER

Rev.1.0–09.2012

1 General Description

RDA5876A integrates industry-lead Bluetooth and FM radio tuner into one chip and is optimized for mobile applications. Bluetooth and FM can work simultaneously and independently, with low power consumption levels target to battery powered devices. For the highest integration level, the required board space has been minimized and customer cost has been reduced. Manufacturers can easily and fast integrate RDA5876A on their product to enable a rapid time to market.

RDA5876A uses CMOS process with a compact 4*4mm 32-pin QFN package.

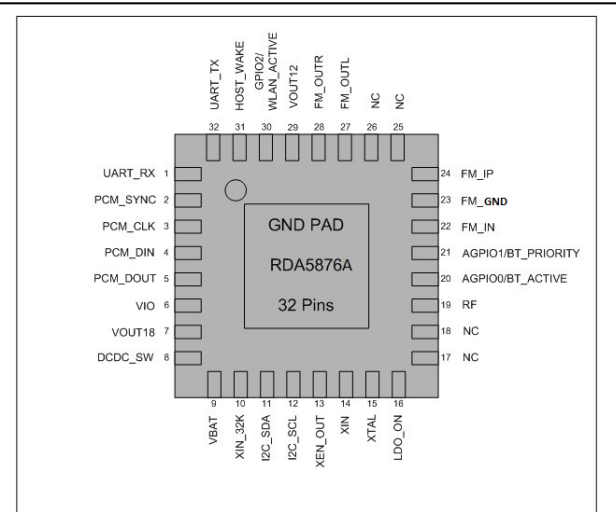


Figure1-1. RDA5876A Top View

1.1 Bluetooth Features

- CMOS single-chip fully-integrated radio and baseband
- Compliant with Bluetooth 2.1 + EDR specification
- Bluetooth Piconet and Scatternet support
- ARM7-based microprocessor with on-chip ROM and RAM
- Meet class 1, 2 and class 3 transmitting power requirement, support class1 operation with external power amplifier
- Provides +10dbm transmitting power
- NZIF receiver with -90dBm sensitivity
- Battery power supply directly with internal LDO
- Support DCXO with internal oscillator circuit
- Up-to 4Mbps high speed UART HCI support
- Support AFH
- Support 3-wire WIFI Co-existence handshake signals
- Low power consumption
- Minimum external component
- Internal 32k LPO.

1.2 FM Features

- CMOS single-chip fully-integrated FM tuner
- Low power consumption
 - Total current consumption lower than 20mA at 3.0V power supply
- Support worldwide frequency band
 - 50 -115 MHz
- Support flexible channel spacing mode
 - 100KHz, 200KHz, 50KHz and 25KHz
- Support RDS/RBDS
- Digital low-IF tuner
 - Image-reject down-converter
 - High performance A/D converter
 - IF selectivity performed internally
- Fully integrated digital frequency synthesizer
 - Fully integrated on-chip RF and IF VCO
 - Fully integrated on-chip loop filter
- Autonomous search tuning
- Support 32.768KHz crystal oscillator
- Digital auto gain control (AGC) Digital adaptive noise cancellation
 - Mono/stereo switch
 - Soft mute
 - High cut
- Programmable de-emphasis (50/75 μ s)
- Receive signal strength indicator (RSSI)
- Bass boost
- Volume control
- Line-level analog output voltage
- I2C control bus interface
- Directly support 32 Ω resistance loading
- Integrated LDO regulator
 - 1.8 to 5.5 V operation voltage

1.3 Applications

- MP3,MP4 and PMP
- PDA
- Cordless phone

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3 Bluetooth Section Functional Description

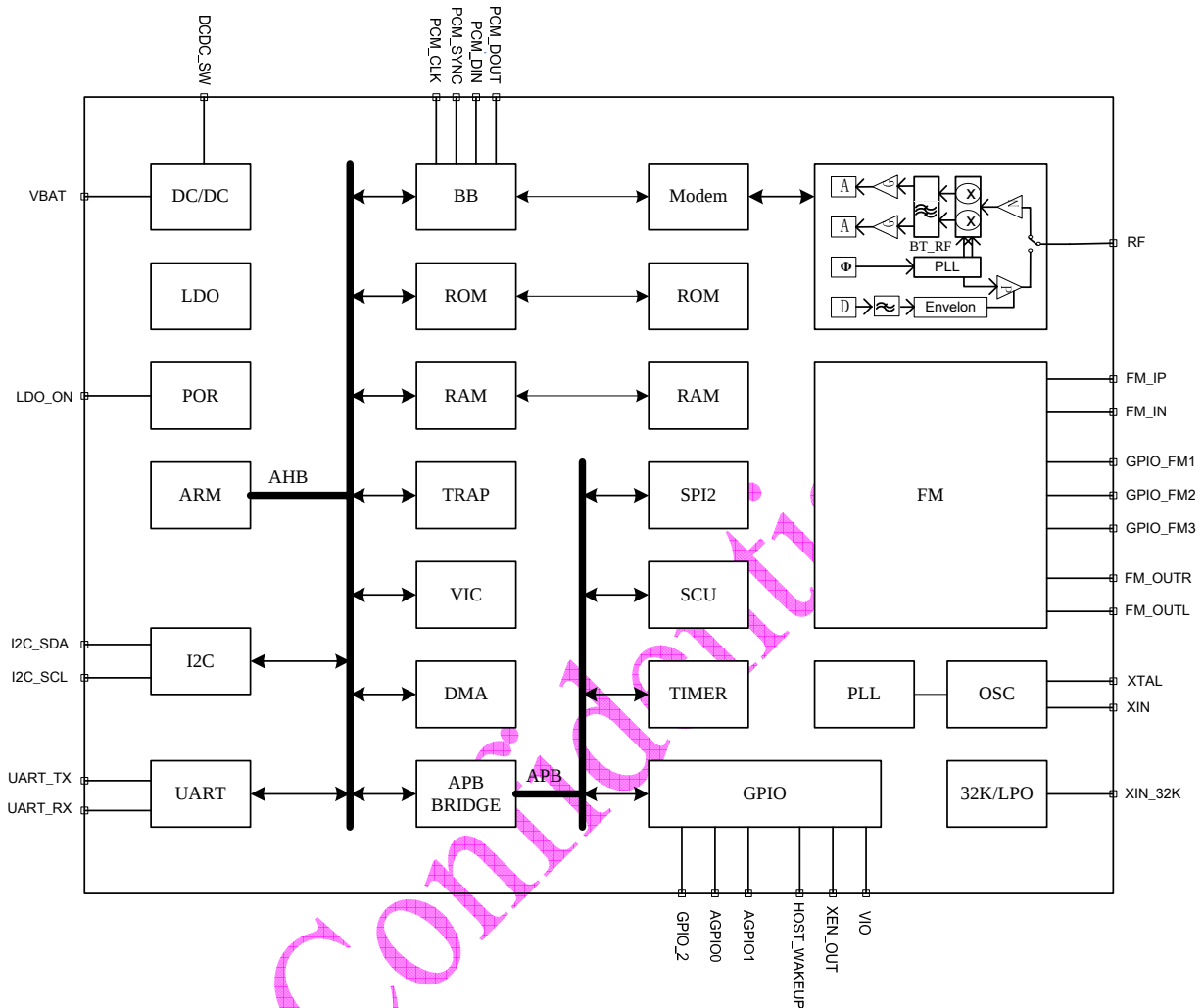


Figure3-1. RDA5876A Bluetooth Block Diagram

RDA5876A is designed for use in UART HCI with handset chipsets. As shown in Figure3-1, RDA5876A integrates radio unit, baseband core, ARM7 core and memory which provides a complete lower Bluetooth protocol stack including the LC, LM and HCI interface.

4 Bluetooth Section Features

■ Radio

- ◆ Build-in TX/RX switch
- ◆ Fully integrated synthesizer without any external component
- ◆ Support DCXO or external reference clock direct input
- ◆ Class1, 2 and class3 transmit output power supported and over 30dB dynamic control range
- ◆ Supports $\pi/4$ DQPSK and 8DPSK modulation
- ◆ High performance in receiver sensitivity and over 80dB dynamic range
- ◆ Integrated channel filter

■ Auxiliary features

- ◆ On-chip regulator to support battery power supply directly
- ◆ Power management support low power mode
- ◆ Support share handset system reference clock
- ◆ Support 3-wire wifi cooperation handshake protocol
- ◆ Support external class1 PA and antenna switch

■ Baseband

- ◆ Internal RAM allows fully speed data transfer, mixed voice and data, and fully piconet operation
- ◆ Logic for forward error correction, header error control, access code correlation, CRC, demodulation, encryption bit stream generation, whitening and transmit pulse shaping
- ◆ Support eSCO and AFH
- ◆ Support up to Bluetooth v2.1 + EDR
- ◆ Support A-law, μ -law and CVSD digitize audio CODEC in PCM interface

■ Interface

- ◆ Provides UART HCI interface, up-to 4Mbps
- ◆ Provides I2C interface for host to do configuration
- ◆ Provides PCM audio interface
- ◆ Provides 3-wire and 2-wire WIFI Co-existence handshake interface

■ Bluetooth Stack

- ◆ Compliant with Bluetooth 2.1 + EDR specification

5 Bluetooth Section Electrical Characteristics

Table 5-1 DC Electrical Specification (Recommended Operation Conditions):

SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNIT
V _{BAT}	Supply Voltage from battery or LDO	3.3	4.0	4.2	V
T _{amb}	Ambient Temperature	-20	27	+50	°C
V _{IL}	CMOS Low Level Input Voltage	0		0.3*V _{IO}	V
V _{IH}	CMOS High Level Input Voltage	0.7*V _{IO}		V _{IO}	V
V _{TH}	CMOS Threshold Voltage		0.5*V _{IO}		V

Notes:

1. V_{IO}=1.8~3.3V

Table 5-2 DC Electrical Specification (Absolute Maximum Ratings):

SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNIT
T _{amb}	Ambient Temperature	-20		+60	°C
I _{IN}	Input Current	-10		+10	mA
V _{IN}	Input Voltage	-0.3		V _{IO} +0.3	V
V _{Ina}	LNA Input Level			+5	dBm

Table 5-3 LDO Power consumption specification

(V_{BAT} = 4.0 V, V_{IO} = 2.8V, T_A = +27°C, RF 9dBm, LDO mode unless otherwise specified)

STATE	DESCRIPTION	Condition	TYP	UNIT
Headset voice	HV3 type		18	mA
Headset SNIFF	500ms cycle	NO INQUIRE and PAGE SCAN	0.5	mA
HCI only active			5.7	mA
Both SCAN	1.28S cycle	INQUIRE and PAGE SCAN	1.0	mA
DeepSleep	26Mhz crystal off	I _{vbat} = 105uA, I _{vio} = 13uA, External 32K input	118	μA
internal LDO off	LDO_ON off	I _{vbat} = 6uA, I _{vio} = 1uA	7	μA

Table5-4 DCDC Power consumption specification(VBAT = 4.0 V, VIO = 2.8V, T_A = +27°C, RF 9dBm, DCDC mode unless otherwise specified)

STATE	DESCRIPTION	Condition	TYP	UNIT
Headset voice	HV3		12	mA
Headset SNIFF	500ms cycle	NO INQUIRE and PAGE SCAN	0.5	mA
HCI only active			3.8	mA
Both SCAN	1.28S cycle	INQUIRE and PAGE SCAN	0.8	mA
DeepSleep	26Mhz crystal off	Ivbat=105uA,Ivio=13uA, External 32K input	118	μA
internal LDO off	LDO_ON off	Ivbat=6uA,Ivio=1uA	7	μA

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6 Bluetooth Section Radio Characteristics

Table 6-1 Receiver Characteristics ----- Basic Data Rate

(VBAT = 4.0 V, TA = 27°C, unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
General specifications						
	Sensitivity @0.1% BER		/	-90	/	dBm
	Maximum received signal@0.1% BER		0	/	/	dBm
	C/I c-channel		/	+10	/	dB
Adjacent channel selectivity C/I	F=F0 + 1MHz		/	/	-5	dB
	F=F0 - 1MHz		/	/	0	dB
	F=F0 + 2MHz		/	/	-33	dB
	F=F0 - 2MHz		/	/	-30	dB
	F=F0 + 3 MHz		/	/	-45	dB
	F=F0 - 3MHz		/	/	-40	dB
Adjacent channel selectivity C/I	F=F _{image}		/	/	0	dB
Out-of-band blocking performance	30MHz~2000MHz		-10	/	/	dBm
	2000MHz~2400MHz		-27	/	/	dBm
	2500MHz~3000MHz		-27	/	/	dBm
	3000MHz~12.5GHz		-10	/	/	dBm
Intermodulation			-35	/	/	dBm
Spurious output level			-150	/	/	dBm/Hz

Notes:

Table 6-2 Transmit Characteristics ----- Basic Data Rate

(VBAT = 4.0V, TA = 27 °C, unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
General specifications						
	Maximum RF transmit power		/	+4	+10	dBm
	RF power control range		25	/	/	dB
	20dB band width		/	0.9	/	MHz
Adjacent channel transmit power	F=F0 + 1MHz		/	-20	/	dBm
	F=F0 - 1MHz		/	-20	/	dBm
	F=F0 + 2MHz		/	-35	/	dBm
	F=F0 - 2MHz		/	-35	/	dBm
	F=F0 + 3MHz		/	-40	/	dBm
	F=F0 - 3MHz		/	-40	/	dBm
	F=F0 + >3MHz		/	/	-46	dBm

	F=F0 - >3MHz	-46	/	/	dBm
$\Delta f_{1\text{avg}}$ Maximum modulation		/	164	/	kHz
$\Delta f_{2\text{max}}$ Minimum modulation		/	145	/	kHz
$\Delta f_{2\text{avg}}/\Delta f_{1\text{avg}}$		0.80	/	/	/
ICFT		/	+4	/	kHz
Drift rate		/	0.1	/	kHz/50us
Drift (1 slot packet)		/	-2	/	kHz
Drift (5 slot packet)		/	-2	/	kHz

Notes:

Table 6-3 Receiver Characteristics ----- Enhanced Data Rate

(VBAT = 4.0 V, TA = 27°C, unless otherwise specified)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$\pi/4$ DQPSK					
Sensitivity @0.01% BER		/	-86	/	dBm
Maximum received signal@0.1% BER		0	/	/	dBm
C/I c-channel		/	/	+13	dB
Adjacent channel selectivity C/I	F=F0 + 1MHz	/	/	+5	dB
	F=F0 - 1MHz	/	/	0	dB
	F=F0 + 2MHz	/	/	-20	dB
	F=F0 - 2MHz	/	/	-20	dB
	F=F0 + 3MHz	/	/	-40	dB
	F=F0 - 3MHz	/	/	-40	dB
Adjacent channel selectivity C/I	F=F _{image}	/	/	-7	dB
8DPSK					
Sensitivity @0.01% BER		/	-83	/	dBm
Maximum received signal@0.1% BER		0	/	/	dBm
C/I c-channel		/	/	+18	dB
Adjacent channel selectivity C/I	F=F0 + 1MHz	/	/	+5	dB
	F=F0 - 1MHz	/	/	+5	dB
	F=F0 + 2MHz	/	/	-20	dB
	F=F0 - 2MHz	/	/	-20	dB
	F=F0 + 3MHz	/	/	-35	dB
	F=F0 - 3MHz	/	/	-35	dB
Adjacent channel selectivity C/I	F=F _{image}	/	/	0	dB

Notes:

Table 6-4 Transmit Characteristics ----- Enhanced Data Rate

(VBAT = 4.0 V, TA = 27°C, unless otherwise specified)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
General specifications					
Maximum RF transmit power		/	+2	/	dBm
Relative transmit control		/	-1.6	/	dB
					kHz
$\pi/4$ DQPSK max w_0		/	+7.4	/	kHz
$\pi/4$ DQPSK max w_i		/	+6.7	/	kHz
$\pi/4$ DQPSK max $ w_i + w_0 $		/	+2.4	/	kHz
8DPSK max w_0		/	+7.1	/	kHz
8DPSK max w_i		/	+4.4	/	kHz
8DPSK max $ w_i + w_0 $		/	+2.7	/	kHz
$\pi/4$ DQPSK Modulation Accuracy	RMS DEVM	/	4.7	/	%
	99% DEVM	/	/	30	%
	Peak DEVM	/	8.8	/	%
8DPSK Modulation Accuracy	RMS DEVM	/	4.6	/	%
	99% DEVM	/	/	20	%
	Peak DEVM	/	11.3	/	%
In-band spurious emissions	F=F0 + 1MHz	/	-14.7	/	dBm
	F=F0 - 1MHz	/	-15.2	/	dBm
	F=F0 + 2MHz	/	-51.0	/	dBm
	F=F0 - 2MHz	/	-51.2	/	dBm
	F=F0 + 3MHz	/	-30	/	dBm
	F=F0 - 3MHz	/	-30	/	dBm
	F=F0 +/- > 3MHz	/	/	-32	dBm
EDR Differential Phase Coding		/	100	/	%

Notes:

7 FM Section Functional Description

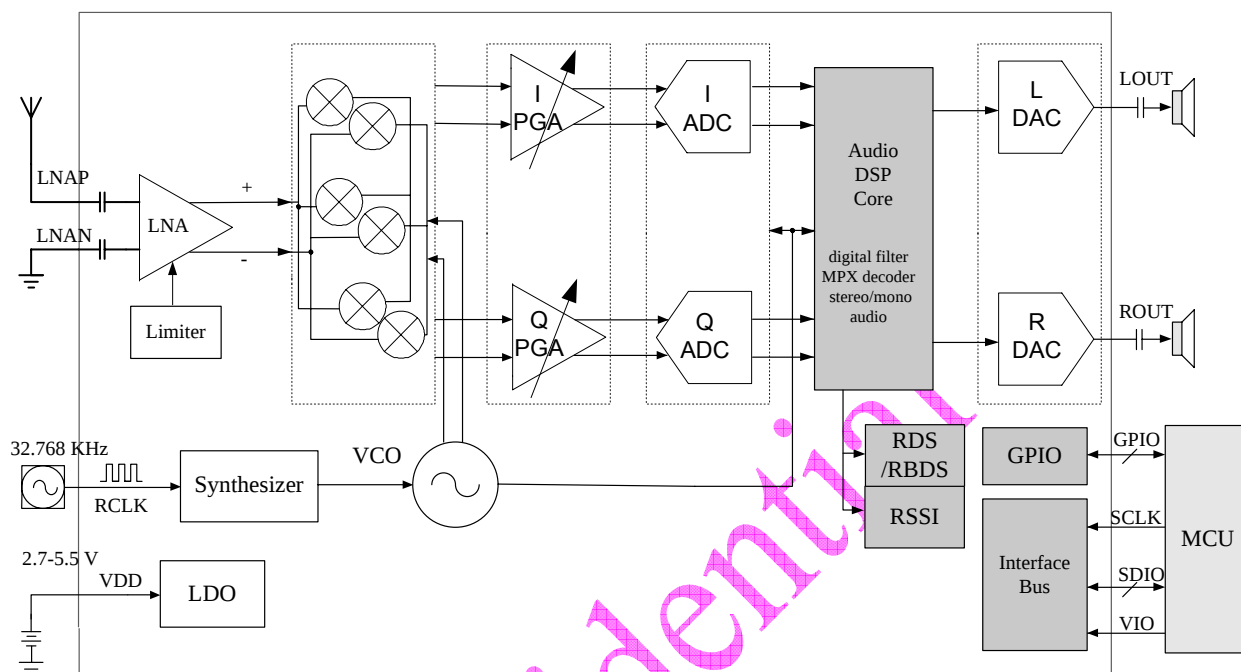


Figure 7-1. RDA5876A FM Tuner Block Diagram

FM Receiver

The receiver uses a digital low-IF architecture that avoids the difficulties associated with direct conversion while delivering lower solution cost and reduces complexity, and integrates a low noise amplifier (LNA) supporting the FM broadcast band (50 to 115MHz), a quadrature image-reject mixer, a programmable gain control (PGA), a high resolution analog-to-digital converters (ADCs), an audio DSP and a high-fidelity digital-to-analog converters (DACs).

The LNA has differential input ports (LNAP and LNAN) and supports any input port by set according registers bits (LNA_port_sel[1:0]). Its default input common mode voltage is GND.

The limiter prevents overloading and limits the amount of intermodulation products created by strong adjacent channels.

The quadrature mixer down converts the LNA output differential RF signal to low-IF, it also has image-reject function.

The PGA amplifies the mixer output IF signal and then digitized with ADCs.

The DSP core finishes the channel selection, FM demodulation, stereo MPX decoder and output audio signal. The MPX decoder can autonomously switch from stereo to mono to limit the output noise.

The DACs convert digital audio signal to analog and change the volume at same time. The DACs has low-pass feature and -3dB frequency is about 30 KHz.

Synthesizer

The frequency synthesizer generates the local oscillator signal which divide to quadrature, then be used to downconvert the RF input to a constant low intermediate frequency (IF). The synthesizer reference clock is 32.768 KHz.

The synthesizer frequency is defined by bits CHAN[9:0] with the range from 50MHz to 115MHz.

Power Supply

The RDA5876A FM section integrated LDO which supplies power to the chip. The external supply voltage range is 1.8-5.5 V.

RESET and Control Interface select

The RDA5876A FM section is RESET itself When VIO is Power up. And also support soft reset by trigger 02H BIT1 from 0 to 1. The control interface is I2C.

Control Interface

The I2C interface is compliant to I2C Bus Specification 2.1. It includes two pins: SCL and SDA. A I2C interface transfer begins with START condition, a command byte and data bytes, each byte has a followed ACK (or NACK) bit, and ends with STOP condition. The command byte includes a 7-bit chip address (0010000b) and a R/W bit. The ACK (or NACK) is always sent out by receiver. When in write transfer, data bytes is written out from MCU, and when in read transfer, data bytes is read out from RDA5876A. There is no visible register address in I2C interface transfers. The I2C interface has a fixed start register address (0x02h for write transfer and 0x0Ah for read transfer), and an internal incremental address counter. If register address meets the end of register file, 0x3Ah, register address will wrap back to 0x00h. For write transfer, MCU programs registers from register 0x02h high byte, then register 0x02h low byte, then register 0x03h high byte, till the last register. RDA5876A always gives out ACK after every byte, and MCU gives out STOP condition when register programming is finished. For read transfer, after command byte from MCU, RDA5876A sends out register 0x0Ah high byte, then register 0x0Ah low byte, then register 0x0Bh high byte, till receives NACK from MCU. MCU gives out ACK for data bytes besides last data byte. MCU gives out NACK for last data byte, and then RDA5876A will return the bus to MCU, and MCU will give out STOP condition.

Details please refer to RDA5876A Programming Guide and RDA5802N Programming Guide and Datasheet.

8 FM Section Electrical Characteristics

Table 8-1 DC Electrical Specification (Recommended Operation Conditions):

SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNIT
VBAT	Supply Voltage	3.3	4.0	4.2	V
VIO	Interface Supply Voltage	1.5	3.0	3.6	V
Tamb	Ambient Temperature	-20	27	+75	°C
VIL	CMOS Low Level Input Voltage	0		0.3*VIO	V
VIH	CMOS High Level Input Voltage	0.7*VIO		VIO	V
VTH	CMOS Threshold Voltage		0.5*VIO		V

Notes:

1. VIO=1.8~3.3V

Table 8-2 DC Electrical Specification (Absolute Maximum Ratings):

SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNIT
VIO	Interface Supply Voltage	-0.5		+3.6	V
Tamb	Ambient Temperature	-40		+90	°C
IIN	Input Current (1)	-10		+10	mA
VIN	Input Voltage(1)	-0.3		VIO+0.3	V
VIna	LNA FM Input Level			+10	dBm

Notes:

1. For Pin: SCL, SDA

Table 8-3 Power Consumption Specification

(VBAT = 4.0 V, VIO=1.5 to 3.6V, TA = -25 to 85 °C, unless otherwise specified)

SYMBOL	DESCRIPTION	Condition	TYP	UNIT
IA	Analog Supply Current	ENABLE=1	20	mA
IVIO	Interface Supply Current	SCL and SDA inactive	90	μA
IAPD	Analog Powerdown Current	ENABLE=0	5	μA
IVIO	Interface Powerdown Current	ENABLE=0	10	μA

9 FM Section Receiver Characteristics

Table 9-1 Receiver Characteristics (VBAT = 4.0 V, VIO= 3.0V, TA = 25 °C, unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	TYP	MAX	UNIT
General specifications							
F _{in}	FM Input Frequency Range	Adjust BAND Register		50		115	MHz
V _{rf}	Sensitivity ^{1,2,3}	S/N=26dB	50MHz	-	1.4	1.8	μV EMF
			65MHz	-	1.2	1.5	
			88MHz	-	1.2	1.5	
			98MHz	-	1.3	1.5	
			108MHz	-	1.3	1.5	
			115MHz	-	1.3	1.8	
IP3 _{in}	Input IP3 ⁴	AGCD=1		80	-	-	dBμV
α _{am}	AM Suppression ^{1,2}	m=0.3		60	-	-	dB
S ₂₀₀	Adjacent Channel Selectivity	± 200KHz		50	70	-	dB
S ₄₀₀	400KHz Selectivity	± 400KHz		60	85	-	dB
V _{AFL} ; V _{AFR}	Audio L/R Output Voltage ^{1,2} (Pins LOUT and ROUT)	Volume [3:0] =1111		-	360	-	mV
S/N	Maximum Signal to Noise Ratio ^{1,2,3,5}		Mono ²	55	57	-	dB
			Stereo ⁶	53	55	-	
α _{SCS}	Stereo Channel Separation			35	-	-	dB
R _L	Audio Output Loading Resistance	Single-ended		32	-	-	Ω
THD	Audio Total Harmonic Distortion ^{1,3,6}	Volume[3:0] =1111	R _{load} =1K Ω	-	0.15	0.2	%
			R _{load} =32 Ω	-	0.2	-	
α _{AOI}	Audio Output L/R Imbalance ^{1,6}			-	-	0.05	dB
R _{mute}	Mute Attenuation Ratio ¹	Volume[3:0]=0000		60	-	-	dB
BW _{audio}	Audio Response ¹	1KHz=0dB ± 3dB point	Low Freq ⁹	-	100	-	Hz
			High Freq	-	14	-	
Pins LNaN, LNAp, LOUT, ROUT and NC(22,23)							
V _{com_rfin}	Pins LNaN/LNAp Input Common Mode Voltage				0		V
V _{com}	Audio Output Common Mode Voltage ⁸			1.0	1.05	1.1	V
V _{com_nc}	Pins NC (22,23) Common Mode Voltage				Floating		V

Notes: 1. F_{in} =65 to 115MHz; F_{mod} =1KHz; de-emphasis=75 μ s; MONO=1; L=R unless noted otherwise;

2. Δf =22.5KHz; 3. B_{AF} = 300Hz to 15KHz, RBW <=10Hz;

5. P_{RF} =60dB μ V;

8. At LOUT and ROUT pins

4. $|f_2-f_1|>1$ MHz, $f_0=2xf_1-f_2$, AGC disable, F_{in} =76 to 108MHz;

7. Measured at V_{EMF} = 1 m V, f_{RF} = 65 to 108MHz

9. Adjustable

10 Pins Description

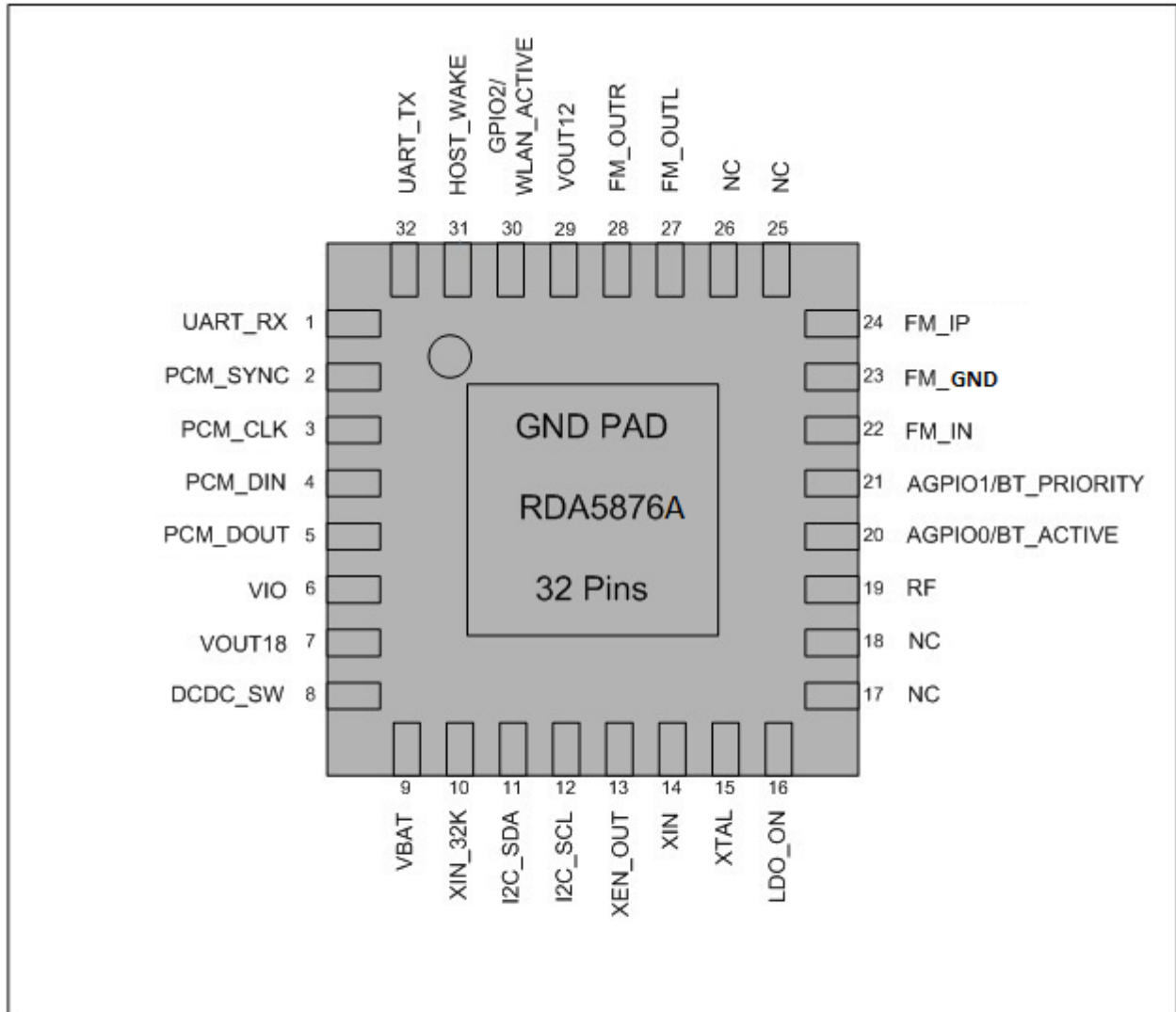


Figure10-1. RDA5876A Top View

Table 10-1 RDA5876A Pins Description

PIN	NO.	DESCRIPTION
UART_RX	1	UART data input
PCM_SYNC	2	Synchronous data sync
PCM_CLK	3	Synchronous data clock
PCM_DIN	4	Synchronous data data in
PCM_DOUT	5	Synchronous data data out
VIO	6	IO power supply
VOUT18	7	Analog voltage output, connected with decouple capacitor
DCDC_SW	8	Internal DC/DC switch voltage output
VBAT	9	Bluetooth and FM power supply
XIN_32K	10	32.768K clock input or external 32.768K crystal
I2C_SDA	11	I2C interface Data signal
I2C_SCL	12	I2C interface Clock signal
XEN_OUT	13	Clock request output
XIN	14	For 26Mhz crystal input or external clock input
XTAL	15	For 26Mhz crystal input
LDO_ON	16	Internal LDO power on
NC	17	Should be not connected
NC	18	Should be not connected
RF	19	Bluetooth Radio signal
AGPIO0	20	Programmable I/O Also used as bt_active when using WIFI co-existence handshake interface.
AGPIO1	21	Programmable I/O. Also used as bt_priority when using WIFI co-existence handshake interface.
FM_IN	22	LNA input port. For single-ended input, LNaN should be connected to RFGND
FM_GND	23	FM ground
FM_IP	24	LNA input port. For single-ended input, LNaN should be connected to RFGND
NC	25	Should be not connected
NC	26	Should be not connected
FM_OUTL	27	Left audio output
FM_OUTR	28	Right audio output
VOUT12	29	Digital voltage output, connected with decouple capacitor
GPIO2	30	Programmable I/O. Also used as wl_active when using WIFI co-existence handshake interface.
HOST_WAKE	31	Output to wakeup host
UART_TX	32	UART data output

11 Package Physical Dimension

Figure12-1illustratesthepackage details for the RDA5876A. The package is lead-free and RoHS-compliant.

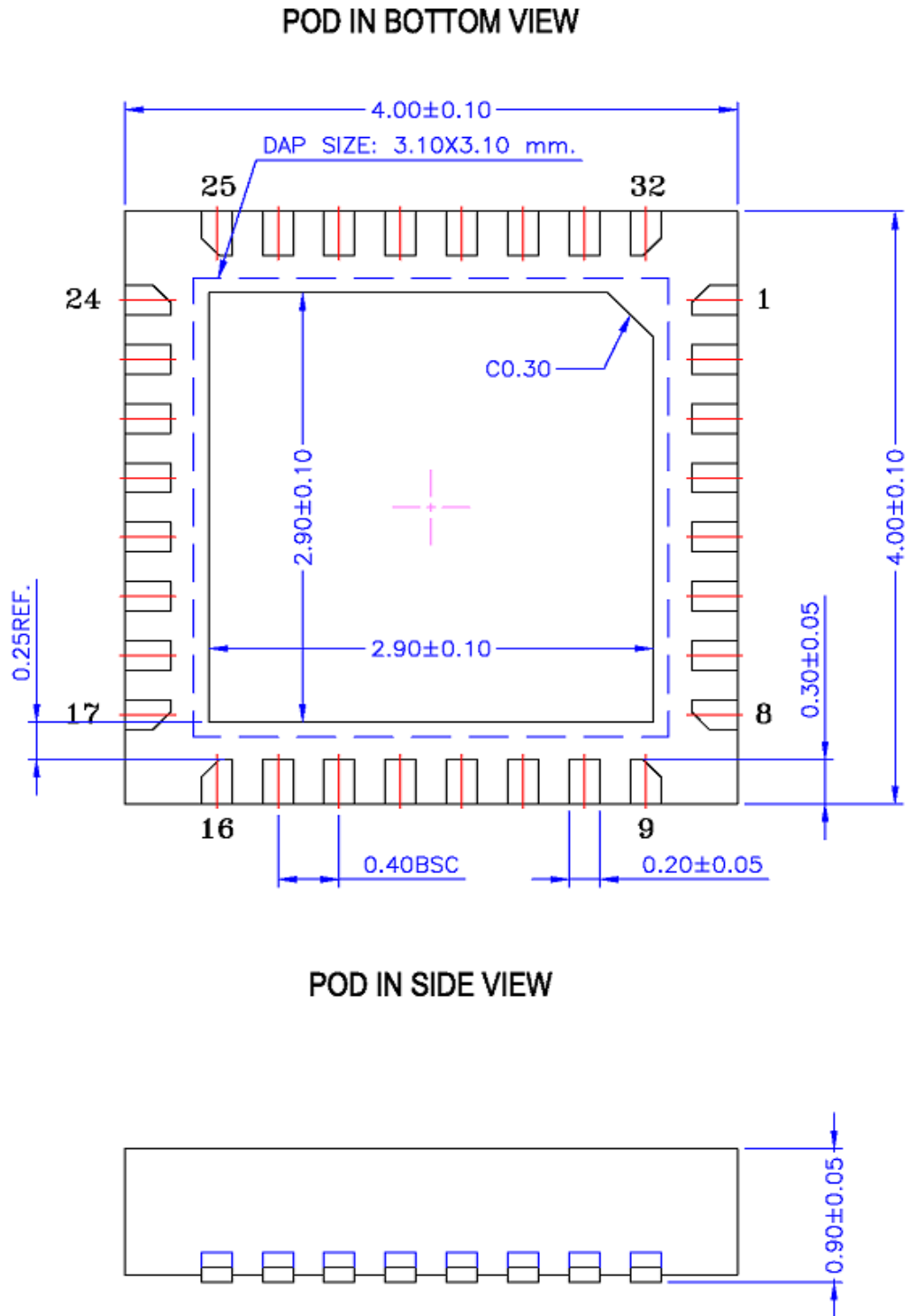


Figure12-1. 32-Pin 4x4 Quad Flat No-Lead (QFN)

12 PCB Land Pattern

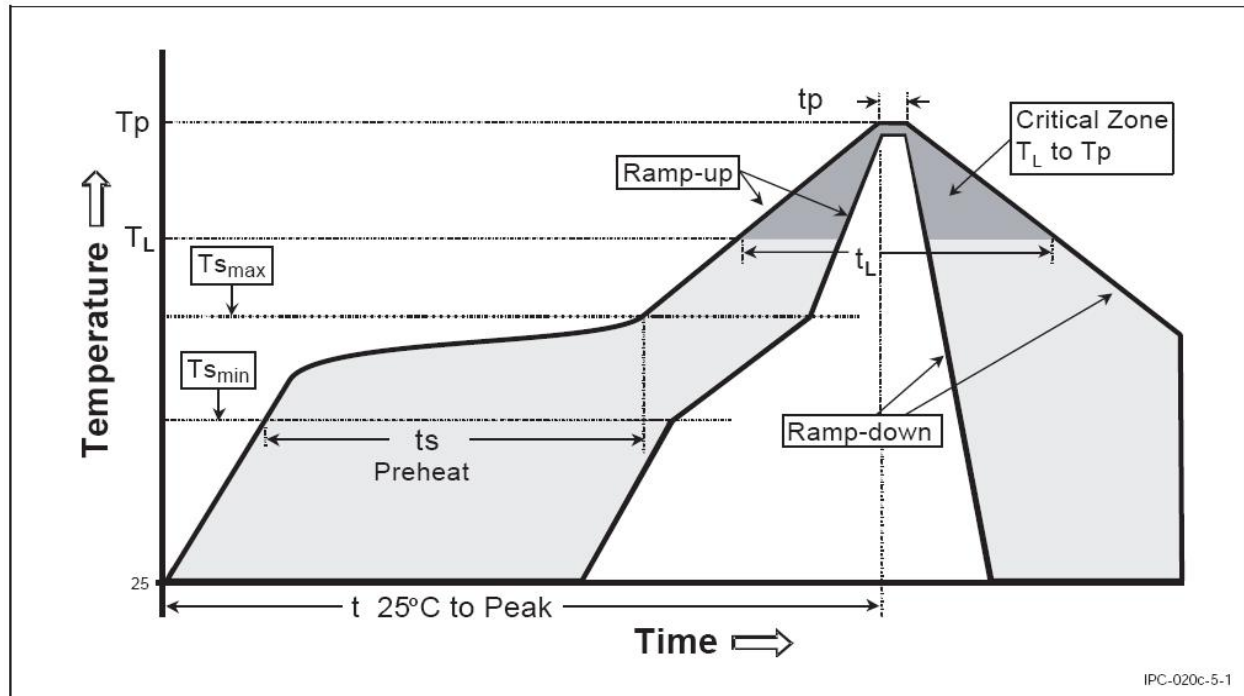


Figure13-3.Classification Reflow Profile

Table 13-1 Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average Ramp-Up Rate (TSmax to Tp)	3 °C/second max.	3 °C/second max.
Preheat		
-Temperature Min (Tmin)	100 °C	150 °C
-Temperature Max (Tmax)	100 °C	200 °C
-Time (tsmin to tsmax)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183 °C	217°C
-Time (tL)	60-150seconds	60-150 seconds
Peak /Classification Temperature(Tp)	See Table 9-2	See Table 9-3
Time within 5 oC of actual Peak Temperature (tp)	10-30 seconds	20-40 seconds
Ramp-Down Rate	6 °C/second max.	6 °C/seconds max.
Time 25 oC to Peak Temperature	6 minutes max.	8 minutes max.

Table 13-2 Pb-free Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm3 <350	Volume mm3 ≥350
<2.5mm	240 + 0/-5 °C	225 + 0/-5 °C
≥2.5mm	225 + 0/-5 °C	225 + 0/-5 °C

Table 13-3 Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm3 <350	Volume mm3 350-2000	Volume mm3 >2000
<1.6mm	260 + 0 °C *	260 + 0 °C *	260 + 0 °C *
1.6mm – 2.5mm	260 + 0 °C *	250 + 0 °C *	245 + 0 °C *
≥2.5mm	250 + 0 °C *	245 + 0 °C *	245 + 0 °C *
*Tolerance : The device manufacturer/supplier shall assure process compatibility up to and including the stated classification temperature(this mean Peak reflow temperature + 0 °C. For example 260+ 0 °C) at the rated MSL Level.			

Note 1: All temperature refer topside of the package. Measured on the package body surface.

Note 2: The profiling tolerance is + 0 °C, - X °C (based on machine variation capability) whatever is required to control the profile process but at no time will it exceed – 5 °C. The producer assures process compatibility at the peak reflow profile temperatures defined in Table 13-3.

Note 3: Package volume excludes external terminals(balls, bumps, lands, leads) and/or non integral heat sinks.

Note 4: The maximum component temperature reached during reflow depends on package the thickness and volume. The use of convection reflow processes reduces the thermal gradients between packages. However, thermal gradients due to differences in thermal mass of SMD package may sill exist.

Note 5: Components intended for use in a “lead-free” assembly process shall be evaluated using the “lead free” classification temperatures and profiles defined in Table13-1, 13-2, 13-3 whether or not lead free.

RoHS Compliant

The product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) or polybrominated biphenyl ethers (PBDE), and are therefore considered RoHS compliant.

ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electricity. Proper ESD techniques should be used when handling these devices.

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13 Change List

REV	DATE	AUTHER	CHANGE DESCRIPTION
V1.0	09/30/2012	Richard C	Initial version.

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14 Contact Information

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